



CHENMKO ENTERPRISE CO.,LTD

CHT1198GP

Halogens free devices

SURFACE MOUNT
PNP Switching Transistor
 VOLTAGE 80 Volts CURRENT 0.5 Ampere

FEATURE

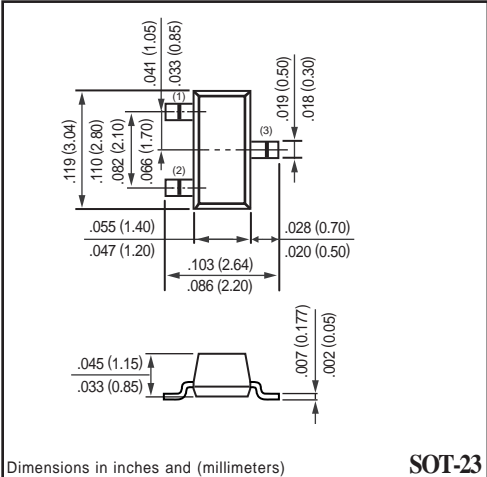
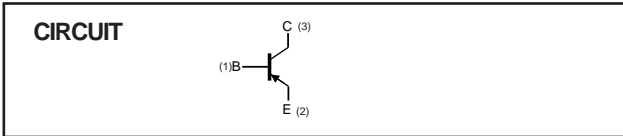
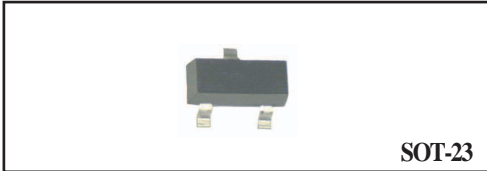
- * Small surface mounting type. (SOT-23)
- * Low Collector-Emitter saturation voltage.
- * High breakdown voltage.

CONSTRUCTION

- * PNP Silicon Transistor

MARKING

- * J22 @hFE as Q Grade
- * J23 @hFE as R Grade



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CB0}	collector-base voltage	open emitter	-	-80	V
V _{CEO}	collector-emitter voltage	open base	-	-80	V
V _{EBO}	emitter-base voltage	open collector	-	-5	V
I _C	collector current DC		-	-0.5	A
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	-	200	mW
T _{stg}	storage temperature		-65	+150	°C
T _j	junction temperature		-	150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

RATING CHARACTERISTIC CURVES (CHT1198GP)

ELECTRICAL CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise noted.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
BV_{CBO}	collector-base breakdown voltage	$I_E = 0; I_C = -50\text{ }\mu\text{A}$	-80	–	V
BV_{CEO}	collector-emitter breakdown voltage	$I_B = 0; I_C = -2\text{ mA}$	-80	–	V
BV_{EBO}	emitter-base breakdown voltage	$I_C = 0; I_E = -50\text{ }\mu\text{A}$	-5	–	V
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = -50\text{ V}$	–	-500	nA
I_{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = -4\text{ V}$	–	-500	nA
h_{FE}	DC current gain	$V_{CE} = -3\text{ V}$; note 1 $I_C = -100\text{ mA}$	120	390	
V_{CEsat}	collector-emitter saturation voltage	$I_C = -500\text{ mA}, I_B = -50\text{ mA}$	–	-500	mV
C_c	collector capacitance	$I_E = I_e = 0; V_{CB} = -10\text{ V}; f = 1\text{ MHz}$	–	11Typ.	pF
f_T	transition frequency	$I_E = 50\text{ mA}; V_{CE} = -10\text{ V};$ $f = 100\text{ MHz}$	–	180Typ.	MHz

Note

1. Pulse test: $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02$.
2. h_{FE} : Q Gade: 120~270
R Gade: 180~390

RATING CHARACTERISTIC CURVES (CHT1198GP)

Figure 1. Grounded Emitter Propagation Characteristics

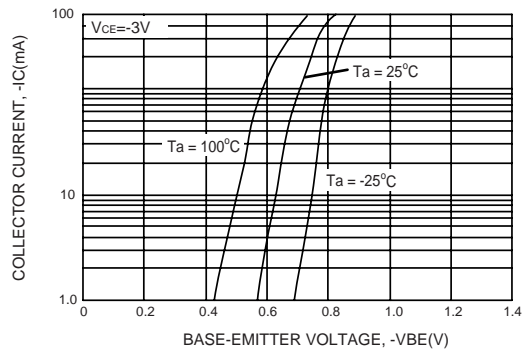


Figure 2. Collector-Emitter Saturation Voltage vs Collector Current

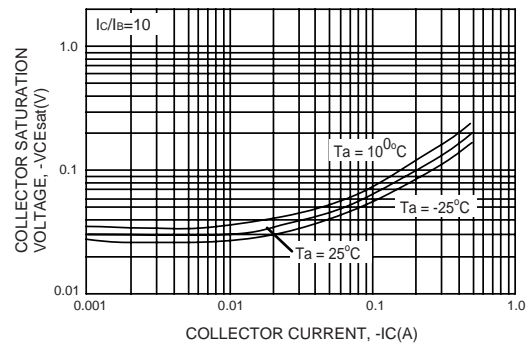


Figure 3. DC Current Gain

